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1	Decomposition of metal alkylamides, alkyls and halides
2	at reducible oxide surfaces: mechanism of 'clean-up'
3	during atomic layer deposition of dielectrics onto III-V
4	substrates
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13 **ABSTRACT:** The pairing of high-k dielectric materials with high electron mobility semiconductors for 14 transistors is facilitated when atomic layer deposition (ALD) is used to deposit the dielectric film. An 15 interfacial cleaning mechanism ('clean-up') that results in consumption of semiconductor native oxides and in practically sharp dielectric/semiconductor interfaces has been observed during ALD of Al₂O₃, 16 HfO₂, TiO₂ and Ta₂O₅ with various degrees of success. We undertake a comprehensive study using 17 18 density functional theory (DFT) to explain differences in the performance of various classes of 19 precursor chemicals in removing native oxide from III-V substrates. The study covers the metals Ta(V), Ti(IV), Zr(IV), Hf(IV), Al(III), Mg(II) combined with methyl, amide and chloride ligands. Of these, we 20 21 show that clean-up is most effective when depositing MgO. Clean-up with metal alkylamides has a 22 similar mechanism to clean-up with metal methyls insofar as oxygen is scavenged by the metal. The 23 difference in operation of alkylamide and methyl ligands lies in the affinity of the ligand to the substrate. Alkylamide is shown to be prone to decomposition rather than the migration of the entire 24 25 ligand evinced by methyl. We investigate the multi-step chemical processes associated with 26 decomposition of alkylamide. These processes can also occur during later cycles of high-k ALD and 27 give a chemical vapor deposition (CVD) component to the ALD process. These transformations lead to 28 formation of clean-up products such as aziridine, ethene, N-methyl methyleneimine, hydrogen cyanide 29 and methane. Some – but not all – of the reactions lead to reduction of surface As_2O_3 (*i.e.* clean-up). 30 These results explain the experimentally-observed accumulation of metallic arsenic and arsenic 31 suboxide at the interface. Such understanding can help achieve control of oxide-semiconductor 32 interfaces through the appropriate choice of chemical precursor.

KEYWORDS atomic layer deposition (ALD), high-*k* dielectrics, III-V substrate, reducible oxide, clean up effect, ALD precursor, metal alkylamide, ligand decomposition, density functional theory (DFT)

35

36 **1. Introduction**

37 The extensive research on pairing of high-k dielectrics materials with high electron mobility 38 semiconductors has renewed interest in replacing SiO₂/Si based transistors for future generations of 39 nanoelectronic devices. The key issue in combining high-k materials for the gate, such as Al_2O_3 and HfO₂, with GaAs or InGaAs III-V semiconductors for the channel is finding a stable passivation of the 40 41 interface with acceptably low density of interface states. Several reports suggest that this can be partially achieved during deposition of the dielectric film using atomic layer deposition (ALD)¹. The early stages 42 43 of ALD growth determine the interface properties and therefore careful optimization of deposition 44 conditions helps with improving device performance. An interfacial cleaning mechanism that results in 45 consumption of semiconductor native oxides and in practically sharp dielectric/semiconductor interfaces has been observed during ALD of Al₂O₃², HfO₂³, TiO₂⁴ and Ta₂O₅⁵ on GaAs and InGaAs. This has 46 been called 'clean-up' or 'self-cleaning'. Although removing native oxides is not sufficient to solve the 47 Fermi-level pinning problem in devices 6 , it is an important step in the preparation of abrupt interfaces. 48 49 The electrical characteristic of the device is improved though when appropriate and optimised passivation and ALD processing is enabled as suggested in ⁷. 50

While the phenomenon of native oxide thinning during semiconductor exposure to ALD metal 51 precursors has been confirmed in several experiments, the chemistry of this process is not well 52 53 understood. First reports on the clean-up effect documented an effective passivation of GaAs-based substrates with trimethylaluminium (TMA or AlMe₃; where Me = CH₃) when depositing Al₂O₃⁸. For 54 HfO₂ ALD, the clean-up effect was observed mainly when using hafnium alkylamides, with similar 55 56 behaviour shown by tetrakis(ethylmethylamido)hafnium (TEMAH or Hf(NEtMe)₄; where $Et = C_2H_5$) or tetrakis(dimethylamido)hafnium (TDMAH, Hf(NMe₂)₄)^{3a, 8-9}. A recent study shows that ALD processes 57 58 utilizing alkylamide precursors featuring Ti (tetrakis(dimethylamido)titanium, TDMAT, Ti(NMe₂)₄) or 59 Ta (pentakis(dimethylamido)tantalum, PDMAT, Ta(NMe₂)₅) also result in the same interfacial cleaning effect while depositing TiO₂ or Ta₂O₅ respectively ^{4b, 5}. These observations indicate that the common 60

for requirement for self-cleaning is the use of organometallic or metalorganic precursors. However, the examples of the purely inorganic $HfCl_4$ and $TiCl_4$ ALD processes contradict this assumption. 'Clean-up' is also observed with the use of these precursors by Delabie *et al.* ^{3b} and Granados-Alpizar and Muscat ^{4a} but was not reported by Frank *et al.* ¹⁰.

65 Common experimental observations are found for interfacial cleaning with TMA and alkylamide 66 precursors. Generally arsenic oxides are easier to remove than gallium oxides. Higher oxidation states of both As (As^{5+}) and Ga (Ga^{3+}) are more sensitive to reduction. Accumulation of metallic arsenic – 67 arsenic suboxide at the interface has been observed for TMA based ALD ^{6a} and alkylamide based ALD 68 69 ⁹. It seems that elevating the temperature of the process significantly enhances the clean-up abilities of alkylamides, and this differentiates these processes from TMA-based clean-up^{5, 11}. Granados-Alpizar 70 and Muscat show differences in surface reactions during GaAs exposure to TMA and TiCl₄ pulses ^{4a}: 71 both precursors remove the native oxide layer, but the mechanisms underlying this process seem to be 72 73 fundamentally different. TMA deposits an Al₂O₃ layer and removes a portion of As from the surface, whereas TiCl₄ removes O and leaves the surface passivated with Cl atoms. The mechanism for 74 75 removing oxides with the use of HfCl₄ differs also from the one for TiCl₄. The growth of hafnium oxide is enhanced ^{3b} and growth of titanium oxide is inhibited ^{4a}. These extensive and sometimes conflicting 76 77 studies on interfacial self-cleaning show how little is understood about the chemistry occurring in the 78 initial cycles of deposition of dielectrics.

In this study with the use of DFT we try to provide improved understanding of the chemical principles underlying 'clean-up' and thus rationalize experimental observations. There are not many studies available on mechanisms during early stages of growth on III-V semiconductors. Typical mechanisms occurring during ALD on other semiconductors (Si, Ge) are described in numerous publications, as reviewed by Elliott ¹². Previous atomic-scale simulations of clean-up mechanisms focused on the interaction of TMA with GaAs ¹³ and III-V native oxides ¹⁴. TMA was shown to be able to reduce arsenic oxides into gaseous As₄ and solid GaAs, with Al₂O₃ formation and C lost as C_2H_6 ¹⁴. DFT 86 revealed that the mechanistic step of reduction takes place when the CH₃ ligand migrates from surface87 bound Al/As/Ga to O and gets oxidised, simultaneously reducing the III-V native oxide substrate. From
88 the TMA example two interesting conclusions emerge: ligand exchange as well as ligand redox
89 mechanisms are at play during clean-up and the precursor metal cation provides an energetic sink when
90 it bonds to oxygen.

91 In the current investigation, building on the example of TMA, we look for an explanation of differences 92 observed in the operation of different families of metal precursors: alkylamides, methyls and chlorides. 93 We focus mainly on the clean-up of the arsenic (III) oxide component of the surface utilizing the 94 $Hf[N(CH_3)_2]_4$ precursor during HfO_2 ALD. The choice of the surface model has been previously motivated and its structure and limitations have been described in detail ¹⁴. The main emphasis here is 95 96 on the interaction of the dimethylamido ligand (dma) with the oxide surface with a view to finding 97 potential redox properties of this ligand. Based on the TMA findings, the metal cation is assumed to be 98 redox inactive, and to combine with oxide anions to form a dielectric oxide. We postulate that formation 99 of the dielectric oxide is the driving force for the clean-up effect and confront this by investigating the 100 clean-up ability of precursors that are chemically different to TMA. Assuming these postulates allows 101 us to define and separate the factors governing the clean-up effect. In this way, a set of general reactions 102 is generated and a comparison can be made between a number of different precursors. In the end, this 103 approach should help with assessing whether clean-up is a general effect, regardless of precursor being 104 used.

105 **2. Computational method & approach**

Periodic density functional theory (DFT) at 0 K as implemented in the VASP package ¹⁵ was applied as a reliable method for computation of the ground state electronic structure and total energy of crystalline materials. We use the generalized gradient approximation (GGA) of Perdew and Wang (PW91) ¹⁶ for the exchange-correlation energy. The core electrons were described with ultrasoft pseudopotentials 110 (USPP) ¹⁷ projected into real space and valence electrons were described with a plane-wave basis with a 111 kinetic energy cutoff of 396 eV. Geometry optimization was carried out with a sparse Monkhorst-Pack 112 *k*-point sampling of reciprocal space. A conjugate-gradient algorithm was used for ionic relaxation with 113 all ions relaxed until the forces on the ions were less than 0.02 eV/Å.

High accuracy was used for bulk oxide calculations: convergence of energies to 10^{-4} eV with respect 114 115 to coordinates of ions and cells, 130% of the standard plane-wave cutoff energy, convergence with 116 respect to k-point sampling. The total energy versus volume for all models of the bulk oxide structures 117 was optimized resulting in equilibrium lattice parameters that agreed well with experiment (with deviation less than 2%)¹⁸. Lattice parameters and space groups, along with k-point sampling for these 118 119 calculations are given in the supporting information. We used experimental lattice constants for the bulk model of *arsenolite* arsenic (III) oxide ¹⁹ since its crystalline structure did not allow us to perform cell 120 shape optimization within DFT as explained in detail before ¹⁴. Ions were fully relaxed within the fixed 121 122 As₂O₃ cell and the structural parameters compared well with the experimental values. The arsenolite-123 As₂O₃ (010) surface is modeled by periodic slabs separated by 10 Å of vacuum. We use a 2×2 surface 124 expansion that contains 1 layer totaling 8 molecular units of As₄O₆ (80 atoms) and a $2 \times 2 \times 1$ k-point mesh for surface calculations. This surface is computed to have a surface energy below 0.02 J/m^2 . 125 126 Gaseous species (precursor molecules and gas phase products) were individually relaxed in a simulation box, cubic or rhombohedral, of dimensions $15 \times 15 \times 15$ Å, with six k-points located at the edges of the 127 128 first Brillouin zone. Geometrical parameters for all optimised gaseous molecules can be found in the 129 supporting information.

For investigation of the ligand decomposition surface reactions we use the bare As₂O₃ (010) surface. For redox reactions differences in Bader atomic charges ²⁰, Δq , are analyzed to determine the chemical state of intermediates and thus help in predicting a final product. The sign convention used in this paper is that $\Delta q < 0$ means loss (oxidation of an atom) and $\Delta q > 0$ means gain (reduction of an atom) of electron population on atoms taking part in the considered reaction. To study the stability of surface bound 135 intermediates we performed DFT molecular dynamics in the canonical ensemble at around 300° C for 136 0.4 ps. At the end of these simulations all surface intermediates were found to be bonded the same as 137 their initial configuration, suggesting that no spontaneous reactions occur and that there are barriers to 138 overcome on the potential energy surface for any following chemical transformations. We neglect the constant contribution to entropy (S) from solid surfaces with adsorbates since S^{trans} and S^{rot} for surfaces 139 are approximately zero and S^{vib} is approximately constant during the reaction, $\Delta S^{\text{vib}} = 0$. Therefore $\Delta S =$ 140 141 0 for surface reactions and the Gibbs free energy profiles closely resemble the DFT potential energy surfaces. Reaction energetics are computed with an estimated accuracy of 0.1 eV. Activation energies 142 reported here were computed using the nudged elastic band method (NEB)²¹. We used up to 8 images 143 144 for each reaction pathway. The damped molecular dynamics algorithm for ionic relaxation was found to 145 be appropriate for the regarded system. Around 1000 steps were needed to converge forces on atoms to 146 below 0.05 eV/Å.

147 In this investigation we consider the process where the adsorbed metal precursor molecules, with the general formula ML_n (M = Mg(II), Al(III), Ti(IV), Zr(IV), Hf(IV), Ta(V); $L = [N(Me)_2]^{-}$, $[Me]^{-}$, $[CI]^{-}$; n 148 149 - oxidation state of metal), undergo a series of clean-up transformations leading to removal of the native 150 oxides of III-V substrates. As outlined in section 1, we propose that the main and most 151 thermodynamically stable product of these transformations is a film of dielectric metal oxide with the 152 general formula M_2O_n . (Thus, there is no reduction or oxidation of *M*). Another factor in the successful 153 clean-up performance is affinity of the precursor ligand L to the III-V oxide substrate. We can describe 154 formation of one O-M bond and subsequent transformations of the ligand on the sample III-V oxide 155 surface (*i.e.* a clean-up process) with the following equation where || stands for surface bound species 156 and g for gas-phase molecules:

157 (1) $||As-O|| + \frac{1}{n} ML_{n(g)} \rightarrow ||O-M_{\frac{1}{n}} + ||As-intermediates; with <math>\Delta E_{\text{clean-up}}$.

158 In the above equation we assume that the formed metal oxide is stoichiometric: upon increasing the 159 coordination number of the metal centre to the native oxide oxygen, the coordination to the ligands 160 decreases and ligands are released to interact with the substrate. The equation also shows that *M*-O 161 formation and interaction of ligands with As can be viewed as separate events, to a first approximation.

Identification of these separate factors allows for an efficient description of interactions of the surface *intermediates* that are formed as a result of ligand decomposition, and of associated chemical processes that lead to formation of the clean-up products. Computing the *intermediates* from just one ligand should be computationally less expensive and easier to understand than computing the decomposition of the entire precursor molecule. Therefore, in this paper we take advantage of this methodology and reduce equation (1) to a description of chemical processes associated only with the interaction of one ligand with the substrate independent of M, as per the reaction:

169 (2) $||As-O|| + HL_{(g)} \rightarrow ||O-H + ||As-intermediates; with <math>\Delta E_L$.

170 A proton is included to ensure overall charge neutrality and so on the right hand side of the reaction a

- 171 hydroxyl group ||O-H| is formed. The formation of one *M*-O bond in equation (1) can then be described
- 172 by the model reaction for various *M*:

173 (3)
$$\frac{1}{n} ML_{n(g)} + \frac{1}{2} H_2O_{(g)} \rightarrow \frac{1}{2n} M_2O_{n(bulk)} + HL_{(g)}$$
; with ΔE_M ,

which is the overall ALD reaction. Combination of the ligand reaction (2) and the metal-dependentcorrection (3) gives essentially reaction (1):

176 (4)
$$\|\text{As-O}\| + \frac{1}{n} ML_{n(g)} \rightarrow M_{\frac{1}{n}} O_{\frac{1}{2} (\text{bulk})} + \|\text{As-intermediates}; \text{ with } \Delta E'_{\text{clean-up}} = \Delta E_L + \Delta E_M,$$

- 177 but at much lower computational effort. Therefore:
- 178 **(5)** $\Delta E_{\text{clean-up}} \approx \Delta E'_{\text{clean-up}}$.

Because of limitations of our current model, we cannot generally compute the complete energetics for each mechanism here. As we focus in this study on the decomposition of the dma ligand and its redox properties, our model naturally does not cover molecular or dissociative adsorption of the precursor and associated steric effects. Nevertheless, for validation purposes we performed explicit simulation of the dissociative adsorption of the whole precursor molecule according to equation (1). In Table 1 we compare energetics obtained for adsorption and ligand dissociation for three different precursors: 185 Hf(NMe₂)₄, AlMe₃, TiCl₄. The 'whole precursor' approach gives a $\Delta E_{clean-up}$ that agrees well with the 186 $\Delta E'_{clean-up}$ value from the 'ligand only' approach in all three cases, thereby strongly supporting the latter 187 approach. Additionally the 'whole precursor' approach for the Hf(NMe₂)₄ precursor was used for the 188 NEB calculation of activation energies, which is reported in the Results and Discussion section.

189

Table 1. Validation of the investigated model: energies $\Delta E_{\text{clean-up}}$ for reaction of precursor adsorption and dissociation of the ligand from the metal center according to reaction $||\text{As-O}|| + \frac{1}{n} ML_{n(g)} \rightarrow ||\text{O-}$ $M_{\frac{1}{n}} + ||\text{As-}L \text{ compared to } \Delta E'_{\text{clean-up}} \text{ obtained from the model 'ligand only' reaction } ||\text{As-O}|| + \frac{1}{n} ML_{n(g)}$ $\rightarrow M_{\frac{1}{n}} O_{\frac{1}{2}(\text{bulk})} + ||\text{As-}L \text{ Surface models showing product of this reaction on the example of Hf[N(Me_2]_4)$ precursor are available in the supporting information. Simulations were performed using identicalcomputational parameters for both approaches.

Metal precursor	$\Delta E_{\text{clean-up}} [\text{eV}]$	$\Delta E'_{\text{clean-up}} [eV]$
Hf(NMe ₂) ₄	-1.0	-1.0
AlMe ₃	-1.2	-1.3
TiCl ₄	-0.2	-0.2

196

197 In section 3.1 thermodynamic energies are presented for formation of metal oxides from gas phase 198 precursors determined using DFT, ΔE_M (equation (3)). In the subsequent sections different types of 199 intermediates that are formed during clean-up as a result of decomposition of selected precursors are 200 examined and their structures are illustrated in Figure 2. Types of reactions included are: dissociation of 201 the precursor through scission of the *M*-*L* bond in section 3.2, decomposition of the dma ligand through 202 scission of the C-H and N-C bonds in section 3.3 and multiple decomposition steps combining these 203 elementary steps described in section 3.4. Energetics for the interaction of ligands with the substrate, 204 ΔE_L , is given in Table 2. The effectiveness of different metal precursors in performing clean-up of III-V 205 oxides is evaluated by correcting ΔE_L with ΔE_M (also Table 2). ΔE_M and ΔE_L along with overall $\Delta E'_{clean}$ -

²⁰⁶ _{up} are summarized in Figure 1 and Figure 3. A reaction scheme considered for the decomposition of the ²⁰⁷ dma ligand is illustrated in Figure 4. A series of proposed elementary steps can give rise to desorption of ²⁰⁸ multiple clean-up products. Based on the thermodynamic accessibility of these elementary surface steps ²⁰⁹ and some kinetic indications, we discuss in each section which clean-up mechanism and associated by-²¹⁰ product is competitive in the ALD process.

211 3. Results and Discussion

212 *3.1. Formation of metal oxides from gas phase precursors*

213 Reaction (3) contains information about the reactivity of precursors towards formation of bulk oxide and 214 bonding changes upon elimination of ligands as H*L*. Computed energetics for a selection of metals and 215 ligands are summarized and illustrated in Figure 1. Values for reaction (3) can be found in Table 2 216 under $\Delta E'_{clean-up}$ for $\Delta E_L = 0$ eV (see equations (3) and (4)).

217

Figure 1. Computed energetics, ΔE_M , for formation of metal oxides from gas phase precursors ML_n (x axis: M = Mg(II), Al(III), Ti(IV), Zr(IV), Hf(IV), Ta(V); $L = [N(Me)_2]^{-}$, $[Me]^{-}$, $[CI]^{-}$; n = oxidation state of metal) and water according to: $\frac{1}{n} ML_{n(g)} + \frac{1}{2} H_2O_{(g)} \rightarrow \frac{1}{2n} M_2O_{n(bulk)} + HL_{(g)}$ (equation (3)). Lines are to guide the eye.



The energetics indicate that the most reactive precursor family for formation of metal oxides and elimination of HL are metal methyls. The most reactive of the six considered is MgMe₂ with $\Delta E_M = -2.7$ eV per methyl ligand. The least reactive among the hypothetical methyl precursors is TaMe₅ with ΔE_M = -1.6 eV per Me for formation of Ta₂O₅. AlMe₃ with ΔE_M = -2.0 eV per Me presents similar reactivity to TiMe₄, not to HfMe₄ or ZrMe₄. Al, Hf and Zr alkylamides with $\Delta E_M \approx -1.0$ eV per ligand have similar reactivity and the Ta and Ti alkylamides are slightly less reactive. The most reactive for formation of oxide among metal alkylamides is Mg[N(CH₃)₂]₂ with $\Delta E_M = -2.1$ eV per alkylamide ligand. According to our computations the smallest driving force for formation of M_2O_n is shown by chloride precursors. ΔE_M for $L = Cl^-$ ranges from -0.5 eV per Cl for Mg to +0.2 eV per Cl for Ta. In general, the calculations reveal the following order of M reactivity, insensitive to the identity of L: $Mg(II) > Hf(IV) \approx Zr(IV) > Ti(IV) > Ta(V)$. The exception is Al(III) which is predicted to change its relative reactivity depending on the nature of L. Relative to the other metals, the Al cation is the most reactive when bonded to chloride ligands and the least reactive, with similar reactivity to Ti(IV), for L =Me $\overline{}$. These trends are consistent with previous calculations 22 .

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Table 2. List of possible clean-up *intermediates*: A-K, A' and A'' that are formed during ALD III-V substrate exposure to various metal precursors. Energies are in eV relative to $||As - O|| + HL_{(g)}$ as per

reaction (2) with $L = [N(Me)_2]^2$, Me⁻, Cl⁻. The effect of different M = Ta, Ti, Zr, Hf, Al, Mg is included by adding the correction ΔE_M obtained from reaction (3) (see section 2 for details).

I	products at surface.		ΔE_L	$\Delta E_L \Delta E'_{\text{clean-up}} \text{ for } M:$					
L	pro	products at surface.		Та	Ti	Zr	Hf	Al	Mg
$[N(Me)_2]^-$		$\ \mathbf{A}\mathbf{s}-\mathbf{O}\ + \mathbf{HNMe}_{2(g)}$	0.0	-0.5	-0.7	-1.0	-1.1	-1.1	-2.1
	A	$ O-H+ As-NMe_2 $	+0.1	-0.4	-0.6	-0.9	-1.0	-1.0	-2.0
	В	$2\ O-H+\ As-N(Me)CH_2-As\ $	+0.6	+0.1	-0.1	-0.4	-0.5	-0.5	-1.5
	С	$2 O - H + As - N(Me)CH_2 - O + 2e^{-1}$	+1.3	+0.8	+0.6	+0.3	+0.2	+0.2	-0.8
	D	$ O - H + As - N(Me)CH_2 - As + As - H - 2e^{-1}$	+2.1	+1.6	+1.4	+1.1	+1.0	+1.0	0.0
	Е	$\ \mathbf{O}-\mathbf{H}+\ \mathbf{A}s-\mathbf{N}(\mathbf{M}e)\mathbf{C}\mathbf{H}_2-\mathbf{O}\ +\ \mathbf{A}s-\mathbf{H}$	+1.2	+0.7	+0.5	+0.2	0.1	0.1	-0.9
	F	O - H + As = NMe + O - Me	+1.5	+1.0	+0.8	+0.5	+0.4	+0.4	-0.6
	G	$ O - H + As = NMe + As - Me - 2e^{-1} O - H + As - Me - 2e^{-1} O - H + As - Me - 2e^{-1} O - H + As - Me - 2e^{-1} O - H + As - Me - 2e^{-1} O - H + As - Me - 2e^{-1} O - H + As - Me - 2e^{-1} O - H + O - H $	+1.6	+1.1	+0.9	+0.6	+0.5	+0.5	-0.5
	H	$3 O - H + As - N(CH_2 - As)_2$	+1.3	+0.8	+0.6	+0.3	+0.2	+0.2	-0.8
	Ι	$4 O - H + As = NCH = CH_2 + 2e^{-1}$	+2.2	+1.7	+1.5	+1.2	+1.1	+1.1	+0.1
	J	$2 O - H + As - N = CH_2 + As - Me$	+0.9	+0.4	+0.2	-0.1	-0.2	-0.2	-1.2
	K	3 O - H + As - N = CH - As + As - Me	+1.9	+1.4	+1.2	+0.9	+0.8	+0.8	-0.2
[Me] ⁻		$\ \mathrm{As}-\mathrm{O}\ +\mathrm{CH}_{4(g)}$	0.0	-1.6	-2.0	-2.2	-2.3	-2.0	-2.7
	A'	$\ O - H + \ As - Me\ $	+0.7	-0.9	-1.3	-1.5	-1.6	-1.3	-2.0
[CI] ⁻		$\ \operatorname{As}-\operatorname{O}\ + \operatorname{HCl}_{(g)}$	0.0	+0.2	+0.1	0.0	-0.1	-0.3	-0.5
	А"	$\ O - H + \ As - Cl$	-0.3	-0.1	-0.2	-0.3	-0.4	-0.6	-0.9

253

254 *3.2. Dissociation of ligand by M-L scission*

By calculating DFT energies for dissociation of the ligand from the metal center, we investigate the affinity of the ligand to the oxide to be cleaned-up. This gives us $\Delta E'_{clean-up}$ for the elementary step that leads to a ligand exchange mechanism. The elementary steps that we have considered involve the transfer of a dimethylamide, methyl and chloride group to the surface As atom in structures **A**, **A'** and 259 A" respectively, shown in Figure 2. Energetics for formation of intermediate A show that the 260 alkylamide ligand can readily dissociate from the M center to the available As site and form a 261 thermodynamically stable product $||As - N(CH_3)_2|$ plus oxide of M (see Table 2 and Figure 3 for 262 energetics). According to reaction (2) and correction for the M-O bond formation, reaction (3), this 263 ligand transfer process is exothermic for all considered metals. The energy for this reaction ranges from 264 -0.4 eV per ligand for Ta[N(CH₃)₂]₅ to -2.0 eV for Mg[N(CH₃)₂]₂. This reaction is very facile with a 265 computed activation energy of just +0.1 eV, and so it will proceed until the surface is saturated with ||As 266 $- N(CH_3)_2$ species (the reaction profile for the corresponding reaction of the whole precursor is 267 available in the supporting information).

268

Figure 2. Surface models for As₂O₃ and decomposition species of metal methyls, A', metal chlorides,
A'', and metal alkylamides, A-K. Stick representation: purple As, red O, white H, gray C, green Cl,
blue N. Selected bond lengths are given in Å. Thin lines show adjacent substrate atoms.

272



273

274 Figure 3. Computed energetics for surface intermediates, A-K, which are formed during clean-up of As₂O₃. As listed in Table 2, A, A' and A'' are surface products of precursor decomposition through 275 276 scission of *M*-*L* bond (M = Mg(II), Al(III), Ti(IV), Zr(IV), Hf(IV), Ta(V)) for $L = [N(Me)_2]^2$, $[Me]^2$, [CI] respectively; **B-E** are surface products of decomposition of [N(Me)₂] through scission of C-H 277 278 bond; F and G surface products of decomposition of $[N(Me)_2]^-$ through scission of N-C bond; H-K are 279 surface products when further decomposition occurs through scission of both C-H and N-C bonds. ΔE_L 280 (equation (2)) describes interaction of the ligand L with the As_2O_3 substrate (black datapoints). It is 281 subsequently corrected with ΔE_M (equation (3)) and gives overall $\Delta E'_{clean-up}$ for various M (equation 282 (4)). Lines are to guide the eye and do not imply a reaction sequence (see instead Figure 4).



283

Energetics show that the methyl ligand is very reactive towards the arsenic oxide substrate and more reactive than alkylamide (**A'** Figure 3). The energy ranges from -0.9 eV for Ta(CH₃)₅ to -2.0 eV for Mg(CH₃)₂. The energy for exchange of a Cl⁻ ligand between the precursor metal center and the native

oxide, with product **A''** in Figure 2, ranges from -0.1 eV for TaCl₅ to -0.9 eV for MgCl₂, indicating that it is less thermodynamically favored than for alkylamides and methyls.

289 Sufficient concentration of these As -L groups may lead to formation of AsL₃: 290 tris(dimethylamino)arsine, TDMAAs, As[N(CH₃)₂]₃; trimethylarsine, As(CH₃)₃ and arsenic trichloride 291 AsCl₃, as volatile products in processes utilizing alkylamides, methyl and chloride precursors respectively. Desorption of these molecules means that As_2O_3 has been transformed into M_2O_n , *i.e.* 292 clean-up. Indeed, this ligand transfer mechanism has been proposed by others ^{3a, 8} to explain the clean-293 294 up effect. Experimental study clearly shows enhancement of the clean-up process with increasing temperature when metal alkylamides are used ^{5, 23}. Even though the first step of the ligand exchange 295 296 reaction is extremely facile, both thermodynamically and kinetically, significant kinetic requirements 297 may originate from steric effects in subsequent steps. There was evidence for this in our previous study 298 for TMA, where we showed that the rate limiting step for the ligand transfer process could be crowding of methyl ligands at one surface site ²⁴. We suspect that this process can be even more difficult for the 299 300 bulkier alkylamides. Thus, steric effects may have a pronounced influence on the kinetics of ligand 301 transfer to TDMAAs, which may stop this reaction before going to completion, and promote ligand decomposition instead. In fact, TDMAAs is known to thermally decompose on the GaAs surface ²⁵. 302 303 Therefore, it is reasonable to suspect that the alkylamide can decompose, or partially decompose, in 304 contact with the native oxide surface, and give rise to other clean-up products rather than form 305 TDMAAs. Ligand decomposition is investigated in subsequent sections.

In the case of chlorides, although they are successfully used in ALD of different metal oxides, there is no agreement in the literature about their interfacial self-cleaning abilities ^{3b, 4a, 10}. One reason may be the lower driving force towards formation of the metal oxide dielectric; Figure 1 shows that formation of the metal oxide during clean-up is an important factor in case of alkylamides and methyls, but a minor factor in the case of chlorides (ΔE_M ranges +0.2 to -0.5 eV). Therefore, we suggest that chloride chemistry is different. Most of the metal chlorides are weak Lewis acids. Their electrophilic characteristic allows them to form Lewis adducts like TaOCl₃, complexes like $[TiCl_6]^{2-}$ or even hydrates, *e.g.* MgCl₂(H₂O)_x ²⁶. Formation of oxychlorides, e.g. TiOCl₂, or even hydroxychlorides, TiCl₃OH, during clean-up with TiCl₄ for TiO₂ deposition, could explain observed removal of O and surface passivation with Cl ^{4a}. As proposed before, clean-up with this ligand can be accounted for via an agglomeration reaction mechanism ^{3b}.

- 317 Ligand affinity for Ga and In is discussed in section 3.5.
- 318 *3.3. Decomposition of dma ligand*

For the following consideration of decomposition processes of alkylamide ligand on the example of dimethylamide we use the highly stable product $\mathbf{A} \| As - N(CH_3)_2$, as a starting species for further cleanup transformations **B-K**. Decomposition of the alkylamide ligand is possible via activation of a C-H bond, releasing anionic or cationic H, or of an N-C bond, releasing anionic or cationic CH₃ as schematically shown in Figure 4. In this section we examine mechanistic paths for these H and CH₃ moieties to attack As and O sites. We consider all possible reactions and highlight redox processes that may enhance the clean-up effect.

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Figure 4. Reaction scheme for decomposition of dimethylamido ligand $[-N(CH_3)_2]^-$ on metal oxide surfaces (species **A-K**). Notation: ' $-H^{+/-}$ ' means dissociation of proton/hydride from ligand to the surface; ' $-Me^{+/-}$ ' means dissociation of methylium/methanide group from ligand to the surface; ' $+2e^{-}$ ' means oxidation of ligand by surface (reduction of surface by ligand); ' $-2e^{-}$ ' means reduction of ligand by surface (oxidation of surface by ligand).



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344 3.3.1. C-H scission and H elimination (B-E)

345 The C-H bond of the ligand is weakened by the electron density of the lone pair of electrons on the 346 neighboring N atom, so that H α to the N atom can dissociate and bond to an available surface site. First 347 we investigate scission of the C-H bond and formation of an O-H bond in the intermediate **B** shown in 348 Figure 2. Our calculations show that upon the proton (H⁺) transfer from a ligand to a surface O atom, 349 the As-O bond is broken. The electronic density around the C atom in the remaining methylene (CH₂) 350 moiety of the ligand increases by $\Delta q = +1.5e$. This Lewis basic C atom can interact with the surface As 351 cation that lost coordination to the O atom. The bond formed between the As atom and the C atom is 2.0 352 Å long which is typical of single As-C bond. As a result a N-methylmethylenimido ion ([-N(Me)CH₂-353 1^{2}) is attached to the surface. Our attempts to find a competitive minimum for the N-354 methylmethylenimido ligand with tricoordinated N atom featuring a N=C double bond (i.e. [-N(Me)=CH₂]⁻) were not successful. The thermodynamically stable state preserves tricoordinated N and 355 356 tetrahedral C. This process is the most exothermic of the decomposition processes with a calculated

 $\Delta E'_{clean-up}$ ranging from +0.1 eV for Ta[N(CH₃)₂]₅ to -1.5 eV for Mg[N(CH₃)₂]₂ (Table 2, **B**). An activation energy of around +1.4 eV is computed for the example of Hf[N(CH₃)₂]₄ where $\Delta E'_{clean-up}$ =-0.5 eV (the reaction profile for the corresponding reaction of the whole precursor is available in the supporting information).

361 We also examine the redox process mediated by ligand attack of the CH₂ mojety onto the O site, instead 362 of the As site, to form product C (Figure 2). This is analogous to the migration of CH_3 from As to O that we observed to be responsible for clean-up with TMA¹⁴. In this elementary step two As-O bonds are 363 364 broken, promoting formation of the O-H (1.0 Å) bond and the O-C bond (1.4 Å). Two electron-deficient 365 surface metal cations are forced to interact and as a result a metallic As-As dimer is formed along with 366 the intermediate $||As - NCH_3CH_2 - O||$. Electrons are transferred to surface arsenic (+1.0e and +1.1e on 367 the dimer atoms) from the C atom of CH₂ (-1.6e) but also from N (-0.5e), elongating the N-As bond by 368 around 2% as compared to structure A. Decomposition of the alkylamide via this process is thus 369 reducing the As oxide surface and contributing to clean-up. This oxidation of the C atom is endothermic 370 for most of the precursors: tantalum, titanium, zirconium amides (+0.8, +0.6, +0.3 eV respectively), 371 almost neutral for hafnium amide (+0.1 eV) and exothermic for magnesium amide (-0.8 eV) according 372 to equations (2) + (3) ($\Delta E'_{clean-up}$, Table 2). It is less favorable than formation of the As-C bond in the 373 structure **B** described above.

374 For completeness we studied scission of the C-H bond and the transfer of H to an As site. This process 375 essentially involves hydride (H⁻) dissociation from the alkylamide ligand and formation of products **D** 376 and E with structures illustrated in Figure 2. In the intermediate D two new bonds are created: As-H and 377 As-C, increasing the coordination number of the As atom from three to five. Formation of these two 378 bonds is expected to cause the withdrawal of the electronic density from the oxide substrate and so its 379 local oxidation (see scheme in Figure 4). Charge analysis suggests a decrease in electronic populations 380 by only -1.0e on the oxidised pentacoordinated As and an increase of +1.0e on the H atom bonded to 381 this arsenic. The absence of charge transfer between this arsenic and CH₂ suggests some charge retraction that is explained as follows. The CH_2 moiety of the created surface product $||As - N(Me)CH_2|$ 382

- As || becomes more Lewis acidic (-0.4e on the C atom) and the N atom more Lewis basic (+0.5e), 383 384 attracting each other (4% shorter N-CH₂ bond, relative to the same bond in **B**) and repelling bonded 385 arsenic atoms (both: As-N and As-CH₂ bonds are elongated by 4%, relative to the same bonds in **B** or 386 C). This indicates that desorption of the N-methylmethylenimido ligand as neutral Me–N= CH_2 should be preferred over formation of the dianion $([-N(Me)CH_2-]^{2-})$ and substrate oxidation. The oxidation of 387 388 As upon hydride dissociation is not favorable. In fact this is one of the least favorable processes that we have computed with energy ranging from +1.6 eV to +1.0 eV for almost all of the precursors and 389 energetically neutral only for Mg[N(CH₃)₂]₂. We observe that no As-O bond is broken in this 390 391 elementary process, *i.e.* it does not contribute to clean-up.

Our results indicate that energy for hydride dissociation can be lowered by 0.9 eV when this process is accompanied by oxidation of the C atom and formation of the surface product **E**: $||As - NCH_3CH_2 - O||$ + ||As - H. In this case As-H and O-C bonds are formed breaking one As-O bond (see Figure 2). We note that electronic densities are withdrawn from the O-CH₂-N entity (-1.0*e*) by the newly-formed hydride (+1.0*e*) and there is no charge transfer to the substrate. The attack of CH₂ onto the O site and transfer of H⁻ to the As site is slightly endothermic for most of the precursors (+0.7 to +0.1 eV) and exothermic for the magnesium precursor (-0.9 eV).

399 DFT calculations show that decomposition of alkylamide ligand through scission of the C-H bond α to 400 N is thermodynamically feasible, but requires quite high activation energy. This pathway is often referred to in the literature as β - H elimination ²⁷. Most likely this process will result in hydroxylation of 401 402 the native oxides and formation of C-As(Ga, In) bonds (B). A possible volatile product of this clean-up 403 transformation is N-methyl methyleneimine (MMI). Desorption of imine in the considered system 404 requires reorganization in the electronic density with the formation of an N=C double bond and 405 cleavage of As-N and As-C bonds, which is consistent with a high activation energy (+1.4 eV for the Hf 406 case; see above). Simultaneously, charge transfer to the surface As should occur resulting in formation 407 of metallic As-As bonds. We calculate that desorption of imine according to the reaction: ||As -

408 NCH₃CH₂ – As $\parallel \rightarrow \parallel$ As-As $\parallel +$ CH₃NCH_{2 (g)} costs +0.7 eV relative to formation of **B**. Thus, the 409 computed reaction energies and high activation energy for the first step suggest that this clean-up 410 pathway producing imine needs elevated temperature for activation.

411 The weakening effect of the N-lone pair on the C-H bonds in the α position has been observed in 412 vibrational spectroscopy, where an unusually low frequency of vibration of the C-H mode in TDMAH has been reported ²⁸. The C-H dissociation is possible already upon adsorption of alkylamide precursors 413 onto silicon substrates at very low temperature of 220 K²⁹. As mentioned in the previous section MMI 414 is a detected product of etching GaAs surface by TDMAAs^{25a}. Several reports can be found where 415 metal alkylamides are shown to decompose to produce imine and amine ³⁰. We show here that H 416 417 elimination can occur from a ligand that has migrated to the native oxide surface $(A \rightarrow B)$. Product B can then undergo other transformations $\mathbf{B} \rightarrow \mathbf{H} \cdot \mathbf{K}$, leading to different clean-up products as described 418 419 later, or desorption of imine can occur. Either process leads to arsenic oxide removal and/or reduction to 420 metallic arsenic, and so may contribute to the clean-up effect.

421 Another clean-up product that can arise from H elimination in the structures **D** and **E** is arsine, AsH₃. 422 However, the unfavourable energetics computed by DFT for elementary steps leading to surface 423 functionalization with ||As - H| groups suggests that formation of arsine from intermediate **D** or **E** is a 424 minor clean-up channel.

425 3.3.2. N-C scission (F-G)

We next examined possible pathways for CH_3 dissociation resulting with products **F** and **G** (for pathways see Figure 4, for structures of products Figure 2). First we considered activation of the N-C bond in the presence of the available Lewis basic O site of the substrate (**F**). As the CH_3 group coordinated to the N atom in the alkylamide ligand has Lewis acidic character (formally CH_3^+ , methylium cation), we expect no redox during transfer to the substrate in this step. Upon this transfer the As-O bond is broken, promoting formation of a double bond between the As and N atoms (1.7 Å). Our results indicate that the reaction along this pathway is moderately endothermic with a

- 433 thermodynamic energy of +1.0 to +0.4 eV for Ta, Ti, Zr, Hf, Al precursors and exothermic by -0.6 eV
- 434 for the Mg precursor ($\Delta E'_{clean-up}$. Table 2).

Another possibility is for the CH₃ moiety to attack an As surface site (**G**). The DFT calculations show that, similarly, an As=N double bond is formed, but As-O bonds are not affected. We observe oxidation of the As atom (-1.9*e*), which is now pentacoordinated, and reduction of the C atom of the dissociated CH₃ moiety (+1.9*e*), consistent with transfer as CH₃⁻ (methanide anion). This elementary step is therefore the reverse of clean-up. The bond formed between the C atom and the As atom is 1.9 Å long. This decomposition structure is a little more unstable than **F** with respect to reactants, at a calculated energy difference of +0.1 eV relative to the energy for formation of product **F**.

442 Pathways involving dissociation of the methyl group lead to functionalization of the surface with ||O -443 CH_3 (F) or formation of the $||As - CH_3|$ groups (G) along with the $||As = NCH_3|$ fragment. This can thus 444 lead to desorption of gaseous dimethyl ether, O(CH₃)₂, or trismethylarsine, As(CH₃)₃. Additionally, if a 445 source of protons is present, methane CH_4 can be formed from $||As - CH_3|$. However, our calculations 446 show that elementary steps for **F** and **G** formation that could give dimethyl ether or trismethylarsine as 447 clean-up products are less competitive when compared to the elementary steps leading to formation of 448 TDMAAs or MMI (A or B, see Table 2). During ALD of metal oxide films, protons can derive from the 449 H₂O pulse, but are supposedly eliminated in reaction with alkylamide ligands to produce amine, the 450 main ALD product. ||O-H groups are also formed during the H elimination process investigated above. 451 We will see later that the sequence of production of **B** and **G** intermediates is competitive and can 452 directly lead to methane production.

- 453 *3.4. Further decomposition of dma ligand*
- 454 3.4.1. Multiple redox steps dehydrogenation H-I

Based on the results shown above, we assume that the main reaction channel for the elimination of H atoms from alkylamide ligands on the oxide substrate is formation of the surface hydroxide and carbonarsenic bound *intermediate* as in product **B**. In this section we investigate the most stable products of successive dehydrogenation of the alkylamide ligand. 459 The stability of the surface intermediate **H** decreases by about 0.7 eV relative to **B** after a second proton 460 transfer. The electronic density increases on both C atoms (+1.2e and +1.3e) and a total of two protons 461 are transferred to the oxide surface. There are now two CH₂ entities that form bonds with acidic As 462 atoms through basic C atoms. A loss of electronic density on N of -0.5e is observed in Bader analysis. 463 This affects the As-N bond, which is weakened (about 8% longer than the As-N bond in product **B**) 464 suggesting that the π character of this bond decreases. The lone pair of electrons on N is no longer 465 stabilized and N becomes nearly pyramidal in this structure (see Figure 2). This process requires energy 466 and so it is clear that it requires some thermal activation.

467 Further dehydrogenation is possible via carbon disproportionation yielding a methylidyne fragment 468 (HC) that inserts into the C-N bond in the intermediate I. The surface product features a double bond 469 between As and N (1.7 Å) that is now bound to a vinyl moiety CH=CH₂ (C=C bond length: 1.3 Å). 470 Three hydroxide groups and an As-As dimer with the bond length of 2.5 Å are formed at the expense of 471 four As-O bonds. Bader analysis confirms reduction of the dimer As atoms (+1.1e and +1.4e for the As 472 atoms bound to N) which means that this reaction contributes to clean-up. We also observe 473 disproportionation of charge between C atoms (increase of electronic population on methylene group of 474 +0.6e and decrease on methylidyne group of -0.3e relative to populations on methyl groups in amide 475 ligand in structure A). We note some charge transfer to the N atom of +0.5e. Formation of an $[=NCH=CH_2]^{2-}$ adsorbate is the most endothermic of the considered processes (+1.6 eV relative to **B** 476 477 formation).

Our computations thus show that successive dehydrogenation becomes progressively less favored. It may result in the formation of the following volatile products: imine from species **B** as mentioned above; aziridine, $HN(CH_2)_2$, from **H**; ethylene, C_2H_4 , and subsequently molecular nitrogen, N_2 , from **I**. The energetics for pathways leading to desorption of these species suggest that this is only possible through thermal activation – moderate temperatures for imine formation and high temperatures for desorption of molecular nitrogen. Aziridine may be produced from structure **H** by a reaction of cleaving As-C bonds, forming a C-C bond (for this process we calculate +0.5 eV relative to formation of **H**), subsequent coupling with adjacent protons if available and desorption, all of which has a DFT energy of just +0.3 eV relative to **H**. This contributes to clean-up, leaving the surface with metallic As-As bonds according to: $||As - N(CH_2 |As||)_2 + ||O - H \rightarrow ||As - O|| + ||As - As|| + HN(CH_2)_{2 (g)}$. The rate limiting step may be breaking As-C and forming a three membered C-C-N ring. Aziridine is one of the stable products detected in the *in situ* mass spectroscopy experiment of thermal decomposition of TDMAAs below 450°C ^{30b}.

491 C₂H₄ was detected as a desorption product originating from secondary surface reactions when a 492 tantalum surface was exposed to Ta[N(CH₃)₂]₅ at 550 K ²⁷. One of the proposed mechanisms envisages 493 dehydrogenation of methyleneimido intermediates, insertion of a methylidyne moiety into the carbon-494 nitrogen bond and subsequent hydrogenation of the vinyl fragment to produce ethylene and leave an 495 adsorbed N atom ²⁷. We suggest that, on the reducible arsenic oxide substrate following coupling of 496 adsorbed N atoms to form N₂ could be possible at highly elevated temperatures, which would result in 497 clean-up according to: 2 ||As = NCH=CH₂ + 2 ||O - H \rightarrow ||As - As|| + 2 C₂H₄ (g) + N₂ (g).

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3.4.2. Multiple redox steps J-K

In this section we study sequences of CH_3 dissociation and alkylamide dehydrogenation reactions that give rise to new clean-up products. Assuming, as previously, that the most probable pathway for alkylamide dehydrogenation is arsenic oxide hydroxylation, we can consider pathways where the CH_3 group formally dissociates either as the methylium cation or as the methanide anion (as the above investigation of processes producing **F** and **G** revealed a competition between them). Here we show the most stable products of these reactions. All other possible reactions can be found in the supporting information.

506 Our investigations suggest that the more stable products are those formed during reactions that do not 507 involve charge transfer to the oxide substrate. For instance, dehydrogenation of the alkylamide ligand 508 followed by dissociation of the methanide anion in structure **J** (Figure 1) is preferred over dissociation 509 of the methylium cation that combined with proton dissociation results in substrate reduction: [–

 $N(CH_3)_2]^- \rightarrow [-N=CH_2]^- + [CH_3]^+ + [H]^+ + 2e^-$ (not showed in Figure 1). The step leading to product J is 510 511 among the few steps that we find to be exothermic or neutral at 0 K for most of the regarded precursors 512 (Table 2). The reorganized electron density in the proton dissociation process (see section 3.3.1 for 513 description of the proton elimination process in structure **B**) can be attracted by a CH_3 group instead of a 514 CH_2 group. Bader analysis shows an increase in the electronic populations on the C atom of CH_3 515 (+1.9e) and decrease on the C atom belonging to the methylene moiety (-1.2e). The acidic methylene forms a double bond with the N atom (1.3 Å), instead of bonding to surface cation like in structure **B**. 516 The basic methanide bonds with the As atom (2.0 Å). We note some increase of electronic density on 517 518 the N atom that is now even more basic (+0.5e) than in the original alkylamide ligand in structure A. 519 Proton dissociation accompanied by the formation of the methanide anion could be a low temperature 520 channel for the formation of CH₄. According to our computations formation of methane from surface 521 intermediate J is slightly exothermic with energy -0.1 eV (neglecting entropy). CH₄ was observed in 522 some studies as a product of decomposition of the amido ligands. Infrared (IR) spectroscopy and 523 temperature-programmed desorption (TPD) investigations of Ti[N(CH₃)₂]₄ on a Si substrate showed that methane desorbs at temperatures below 400 K^{29b}. In the same study DFT calculations suggest that 524 525 facile generation of methane right above room temperature is due to the surface activation of C - H and 526 C - N bonds of amido ligand. In the thermal chemistry investigation of Ta[N(CH₃)₂]₅ CH₄ is a decomposition product detected throughout the studied temperature range up to 600 K²⁷. Our DFT 527 528 results suggest that scission of the N-C bond is triggered by the H elimination process on the oxide 529 substrate and thermodynamically is not as demanding as other decomposition processes. Although 530 formation of methane is plausible, desorption of this chemical alone from the oxidised III-V system 531 does not directly result in self-cleaning. In this pathway methane is formed according to: ||As - Me + ||O|| $-H \rightarrow ||As - O|| + CH_4$, so arsenic oxygen bonds are formed. However, other products can arise as a 532 533 consequence of saturation of the native oxide surface with $[-N=CH_2]^-$ groups after CH₄ desorption in species J: C₂H₄ and subsequently N₂. Eventual desorption of CH₄, C₂H₄ and N₂ would finally lead to 534 clean-up resulting in reduction of arsenic oxide to metallic arsenic, but involving multiple redox steps: 2 535

536 $||As - N = CH_2 \rightarrow ||As - As|| + C_2H_4 _{(g)} + N_2 _{(g)}$. This process requires energy to break the double bond 537 between N and C atoms, combining two CH₂ groups and two N moieties on the surface. As remarked in 538 our discussion of possible products arising from *intermediate* I, processes involving multiple redox 539 steps are presumably possible at highly elevated temperatures.

540 Further dehydrogenation of the methylene group in the $[-N=CH_2]^-$ adsorbate described above, yields a 541 methylidyne (CH⁺) ion in surface product **K**. This is less favored by +1.0 eV relative to previous 542 process J (see Table 2). Proton dissociation to another O site renews C basicity (+1.0e with respect to the $[-N=CH_2]^-$ adsorbate) that now can attack another As site. The $[-N=CH_2]^{-1}$ ion is bound to surface 543 544 arsenic atoms through N and C, forming bonds 1.9 Å and 2.0 Å long respectively (K Figure 1). Generation of the $[-N=CH-]^{2}$ -surface intermediate can directly lead to desorption of hydrogen cyanide, 545 HCN, another clean-up product: $||As - N = CH - As|| \rightarrow ||As - As|| + HCN_{(g)}$. HCN was detected to 546 desorb at 600 K during tantalum alkylamide exposure to a tantalum substrate ²⁷. 547

548 3.5 Effect of substrate on clean-up

549 Our model supposes that clean-up can be achieved by successive dissociation of ligands from the 550 absorbed precursor. One can expect that the M - L bond can be easily activated on the oxide surface 551 when the substrate metal oxide is less stable than the deposited metal oxide M_2O_n . The metal center of 552 the precursor then becomes chemically active towards penetrating the III-V oxide substrate and 553 scavenging the oxygen. A similar technique is used for equivalent-oxide-thickness scaling for complementary metal-oxide-semiconductor devices ³¹. With different variations scaling is achieved via 554 555 a scavenging reaction between the scavenging element (metal) and SiO₂ and the driving force is also formation of the metal oxide rather than maintaining SiO₂. We showed previously that the driving force 556 of the clean-up effect is removing As(Ga, In) – O bonds and forming M – O bonds ^{14, 31}. As has lower 557 558 electropositivity and therefore lower affinity to O than the metals considered: Mg, Hf, Zr, Ti, Ta and Al. 559 In thermodynamic equilibrium, formation of any of the oxides of these metals is assumed to be favored 560 over formation of the As oxide. DFT energetics for the ligand exchange mechanism supports this supposition, independent of the ligand in use (see Figure 3 A, A' and A''). Among the III-V elements 561

562 (As, Ga, In) it is again As that has the lowest electropositivity and forms the weakest oxides. To 563 emphasize this we calculate from first principles bulk energies for ligand exchange between the 564 regarded precursors and Ga(III) and In(III) native oxides and compare them with the exchange energy 565 for As(III/V) native oxide:

566 (6) $\frac{1}{n}ML_n (g) + \frac{1}{2m}N_2O_m (bulk) \rightarrow \frac{1}{2n}M_2O_n (bulk) + \frac{1}{m}NL_3 (g)$, with ΔE_{L_ex} , where N = As(III), As(V),

567 Ga(III), In(III); m = oxidation state of N.

568 Figure 5 shows the energetics for the above reaction on the example of alkylamide precursors (L =569 [NMe₂]). It is clearly seen that As₂O₃ is the weakest and the most reactive among these native oxides 570 towards exchanging O with ligands and therefore is the easiest to clean-up. It seems that In oxide resists 571 clean-up more than Ga oxide and is less likely to bind to ligands at the surface. As(III) and As(V) oxides 572 are seen to have similar reactivity for ligand exchange, with the exception of Al[NMe₂]₃ that seems to 573 have greater affinity for As(III). We observe no oxidation state dependency for the ligand exchange mechanism, contrary to the suggestion of Hinkle et al⁸. This result holds true for different ligands (see 574 575 supporting information).

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Figure 5. Computed energetics for ligand exchange of alkylamide between precursor metal center and bulk III-V oxide: As₂O₃, As₂O₅, Ga₂O₃ and In₂O₃ according to: $\frac{1}{n}ML_{n (g)} + \frac{1}{2m}N_2O_{m (bulk)} \rightarrow \frac{1}{2n}M_2O_n$ (bulk) + $\frac{1}{m}NL_3$ (g) for M = Mg(II), Al(III), Ti(IV), Zr(IV), Hf(IV), Ta(V), $L = [N(Me)_2]^-$; n =oxidation state of M; N = As(III), As(V), Ga(III), In(III); m = oxidation state of N. Lines are to guide the eye.



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590 Additionally, ligands left on the surface can enhance the clean-up effect by interacting with the substrate 591 and this depends on the affinity of the ligand to the substrate and on the chemical character of the substrate. We consider first ligand affinity. Metalloid oxides, like AsO_x, are susceptible to reduction in 592 contact with reducing agents, *e.g.* by the methanide anion Me⁻ in TMA as we showed previously ¹⁴ or by 593 594 CH₂ from deprotonated alkylamide (section 3.3.1, C). Self-cleaning by TMA was shown to be governed 595 by mobility of the methyl group, which undergoes oxidation, transferring electrons to the surface. 596 Various elementary steps were found to be thermodynamically competitive and to lead to a surprising 597 range of by-products. However, dma [NMe₂]⁻ and chloride Cl⁻ anions are not as strong reducing agents 598 as Me⁻. This is supported by DFT energies, shown in Figure 6, for reactions of transferring those ligands 599 from the metal center of the precursor to a surface O site on the As₂O₃ substrate. Formation of ||O - L|600 surface intermediates causes reduction of metalloid oxides:

601 (7) 2 $\|\text{As-O}\| + \frac{1}{n} ML_{n(g)} \rightarrow M_{\frac{1}{n}} O_{\frac{1}{2}(\text{bulk})} + \|\text{O-}L + \|\text{As-As}\| \text{ with } \Delta E_{L \text{ ox.}}$

In Figure 6 we can see that the chloride ligand, almost independently of which metal center it is bound to, is resistant to oxidation with $\Delta E_{L_{ox}}$ around +2.5 eV. The same holds for dma with $\Delta E_{L_{ox}} \approx +1.2$ eV, except for Mg(NMe₂)₂ that can dissociate its ligand to the O in the As₂O₃ substrate with $\Delta E_{L_{ox}}$ a little below 0 eV. On the contrary, the methyl group is always susceptible to oxidation with exothermic $\Delta E_{L_{ox}}$ for all metal precursors selected.

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Figure 6. Computed energetics for ligand oxidation at the surface, $L = [N(Me)_2]^-$, $[Me]^-$, $[Cl]^-$, and As₂O₃ reduction according to: $||As-O|| + \frac{1}{n}ML_{n (g)} \rightarrow M_{\frac{1}{n}}O_{\frac{1}{2}(bulk)} + ||O-L + ||As-As||$ for M = Mg(II), Al(III), Ti(IV), Zr(IV), Hf(IV), Ta(V). Lines are to guide the eye.



612

The second factor affecting clean-up is substrate chemistry. If a ligand is susceptible to decomposition, specific sites on the surface can activate some bonds of the ligand and this can trigger secondary surface reactions that result in clean-up. C-H and N-C bonds of the dma ligand can be activated even at relatively low temperature as discussed in previous sections. It has been shown that especially mixed nucleophilic-electrophilic character of the surface sites, *e.g.* the zwitterionic character of silicon, affects reactivity and transformations of alkylamides ²⁹. Such reactivity of alkylamides is confirmed by experimental observation of formation of Si-H bonds accompanied by the formation of Si-C bonds

620 (leading to incorporation of carbon into the deposited film). Low temperature production of methane has 621 also been observed, which is evidence for N-C reactivity when depositing oxide films on bare Si or 622 hydrogen terminated Si substrates. In our calculations, we see similar behaviour of the alkylamide ligand on the relatively weakly amphoteric As₂O₃ substrate. On this oxide substrate H is removed from 623 624 the ligand as a proton and formation of O-H bonds is plausible. In this process clean-up is achieved, as 625 well as producing additional reactive sites (OH) for ALD, but at the same time *M*-C bonds are formed. 626 This is because proton elimination causes changes in electronic density on alkylamide carbons: the CH₂ 627 fragment becomes Lewis basic and this promotes M-C formation (**B**), or the CH₃ fragment attracts the 628 charge, and CH_3^- detachment is promoted, resulting also in *M*-C formation (**J**). Some of these reactions may be more strongly favoured on the mixture of more electropositive Ga³⁺ and In³⁺ sites of the real III-629 V surfaces or even the M^{n+} sites of the growing film, where bonds tend to be more ionic rather than 630 631 covalent. Based on this we can conclude that the above-mentioned mechanisms account for the 632 reactivity and behaviour of metal alkylamides and can be expected on various substrates featuring Lewis 633 acid/base sites.

634 An important aspect is whether these processes occur during homodeposition (*i.e.* during the later stages of growth of e.g. HfO₂ onto HfO₂) and give a CVD component to standard ALD. Clearly during 635 636 homodeposition there is no extra driving force from M_2O_n formation. On the other hand, decomposition 637 reactions may be more favoured on the growing film owing to its pronounced nucleophilic-electrophilic 638 or Lewis acid/base character, as mentioned above. According to our computations, processes yielding 639 B-K are energetically uphill from formation of intermediate A onwards. However the formation of B 640 and J are only +0.5 eV and +0.8 eV uphill respectively at 0 K for the clean-up process on the As₂O₃ 641 substrate and can be expected at elevated temperatures. This finding is supported by experimental 642 observation of increased efficiency of clean-up with increased temperature. Another aspect is simple 643 consideration of the strength of the As-O bond and, using the example of HfO₂, the Hf-O bond. Clearly 644 the Hf-O bond, once it is formed, is much stronger and less reactive, which does not favour subsequent 645 CVD reactions. An explicit investigation of CVD reactions on the HfO₂ surface is necessary to fairly 646 judge the importance of the CVD contribution in case of alkylamide ALD, but is beyond the scope of 647 this paper.

648 **4. Conclusion**

649 We successfully apply our model for clean-up to explain differences in the performance of various 650 classes of precursor chemicals in removing native oxide from III-V substrates. Building on the example 651 of TMA, we identify two separate factors governing the clean-up effect: formation of the metal oxide as 652 the primary driving force and affinity of the precursor ligand to the III-V oxide substrate as the ancillary 653 force. That allows an efficient description of interactions of the various precursor ligands with an 654 oxidised III-V substrate, and of the associated multi-step chemical processes that lead to formation of 655 the clean-up products. We map out reaction sequences for the alkylamide ligand that lead plausibly to 656 products that are detected experimentally (aziridine, ethylene, MMI, HCN, methane). Through this 657 approach, a set of general reactions is generated and comparison is made between several different 658 precursors, including metal alkylamides Mg[N(CH₃)₂]₂, Al[N(CH₃)₂]₃, Ti[N(CH₃)₂]₄, Zr[N(CH₃)₂]₄, 659 Hf[N(CH₃)₂]₄, Ta[N(CH₃)₂]₅; metal methyls: Mg(CH₃)₂, Al(CH₃)₃, Ti(CH₃)₄, Zr(CH₃)₄, Hf(CH₃)₄, Ta(CH₃)₅; and metal chlorides: MgCl₂, AlCl₃, TiCl₄, ZrCl₄, HfCl₄, TaCl₅. We can therefore predict the 660 661 best reagent for achieving the clean-up effect.

We predict that the investigated methyl precursors are the best reagents for deposition of dielectrics and performing clean-up. Unfortunately, most of them are very unstable compounds. Clean-up is most effective when depositing MgO, as Mg^{2+} works as the most effective scavenger of O^{2-} . Clean-up with metal chlorides seems to have a fundamentally different mechanism, probably involving removal of the O from the native oxide film and passivation with Cl groups.

The first principles study shows that clean-up with metal alkylamides has a similar mechanism to cleanup with metal methyls as regards the scavenging of oxygen from weak As, Ga and In oxides. Arising from this, ligand exchange can in principle lead to a clean-up product: tris(dimethylamino)arsine. However steric hindrance and the bulky character of the alkylamide ligand are rate limiting factors,which in this case are very pronounced and suggest that this particular reaction will not proceed.

672 Our study also shows the difference in mechanism underlying the consumption of III-V oxides with 673 alkylamido precursors from the one taking place with TMA. In the case of the alkylamide ligand, 674 thermal decomposition rather than migration of the entire ligand on the oxide surface is dominant, 675 taking into account the bulky character of the ligand and its known reactivity in contact with a 676 semiconductor or metallic surface. Clean-up of the reducible As oxide substrate is therefore enhanced 677 by secondary decomposition surface reactions, not by oxidation of the entire alkylamide. The H 678 elimination process that forms hydroxyl groups and As-C bound species (B) is exothermic or neutral at 679 0 K and kinetically demanding. The migration of these decomposition intermediates from an As site to 680 an O site (C) and direct reduction of the substrate is only slightly endothermic. Successive 681 dehydrogenation though becomes progressively less favored. Instead, the first H elimination may be 682 followed by another plausible reaction - N-C bond scission (J), which can lead to low temperature 683 methane production, albeit without the clean-up effect. Thermal activation is needed for formation and 684 desorption of products that arise from these decomposition structures: most likely N-685 methylmethyleneimine and aziridine, possibly along with methane, ethylene and dinitrogen. A specific 686 requirement of the substrate is that it contain both Lewis acid and Lewis base sites, which can activate 687 secondary surface reactions of ligands that are susceptible to decomposition, like the dimethylamido 688 group. These redox processes do lead to the reduction of arsenic oxides to metallic arsenic, which in 689 turn can reduce gallium and indium oxides to pure III-V material. Some of the reactions that we have 690 presented therefore account for the clean-up effect, but they occur in parallel with reactions that do not 691 achieve clean-up.

More generally we show that organometallic reagents react readily with substrates featuring less electropositive metals. In presence of metals like Si, As, Ga and In, a reactive polar metal-organic ligand bond, *e.g.* Al-C, is broken and formation of more covalent bond, *e.g.* As-C, is favoured. These reactions might be possible during homodeposition and can thereby give a CVD component to standard ALD, as
is well-documented for alkylamides. The mechanisms described here are in line with observations on Si
surfaces as well. The same mechanisms can therefore be expected on other substrates, such as oxides
and nitrides, that show a mix of Lewis acid/base sites.

699

700 ASSOCIATED CONTENT

Supporting Information Available: lattice parameters and space groups, along with *k*-point sampling for optimised bulk structures; geometrical parameters for optimised gaseous molecules; additional list of possible clean-up *intermediates* that are formed during ALD III-V substrate exposure to alkylamide metal precursors – energetics for the interaction of dma ligand with the substrate (ΔE_L); surface models showing products of the dissociative adsorption of Hf[N(CH₃)₂]₄ precursor; reaction profile for dissociative adsorption of Hf[N(CH₃)₂]₄ precursor; energetics for ligand exchange between precursor metal centre and bulk III-V oxide: As₂O₃, As₂O₅, Ga₂O₃ and In₂O₃ for *L* = [Me]⁻; [Cl]⁻.

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- The authors declare no competing financial interest.

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- 843 layer deposition technique (ALD) with the appropriate precursor chemical is used during transistor
- 844 fabrication.
- 845